Am4025/5025 · Am4026/5026 · Am4027/5027

2048-Bit Dynamic Shift Registers

Distinctive Characteristics

- 6 MHz data rate guaranteed
- Single 2048 and dual 1024-bit configurations
- Low power dissipation
- TTL compatible data inputs and outputs

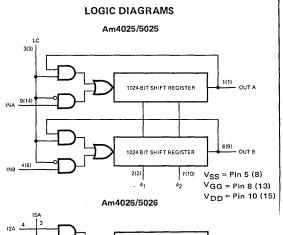
- On chip recirculate and input select controls
- Alternate source to National parts
- Full military temperature range devices available
- 100% reliability assurance testing in compliance with MIL-STD-883

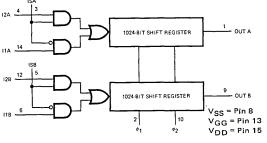
FUNCTIONAL DESCRIPTION

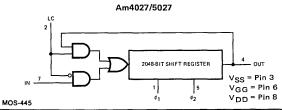
The Am4025/6/7 and Am5025/6/7 are military and commercial grade 2048-bit dynamic shift registers. Am4025/5025 is a dual 1024-bit device with on-chip recirculate and a load control (LC) common to both registers. When LC is HIGH, the two registers recirculate data; when LC is LOW new data is entered through the data inputs. The Am4026/5026 is similar, but each register has two data inputs, selected by separate input select (IS) signals. The Am4027/5027 is a single 2048-bit register with on-chip recirculate and a load control. All the devices can drive one standard TTL load or three Am93L series low-power TTL loads. The select, load command, and data inputs may be driven by TTL signals. Two high-voltage clock signals, ϕ 1 and ϕ 2, are required. Internally, each shift register consists of two multiplexed registers, so that a data shift occurs on each ϕ 1 or ϕ 2 clock pulse. The data rate, therefore, is double the frequency of either clock signal.

ORDERING INFORMATION

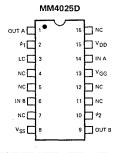
Package	Temperature	Order
Туре	Range	Number
10-Pin Molded	0°C to +70°C	MM5025N
16-Pin Hermetic	0°C to +70°C	MM5025D
16-Pin Hermetic	–55°C to +125°C	MM4025D
16-Pin Molded	0°C to +70°C	MM5026N
16-Pin Hermetic	0°C to +70°C	MM5026DC
16-Pin Hermetic	–55°C to +125°C	MM4026D
8-Pin Molded	0°C to +70°C	MM5027N
8-Pin Hermetic	0° C to $+70^{\circ}$ C	AM5027DC
8-Pin Hermetic	–55°C to +125°C	AM4027DM

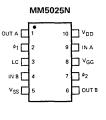


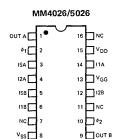


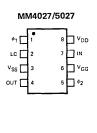


CONNECTION DIAGRAMS Top Views









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MAXIMUM RATINGS (Above which the useful life may be impaired)

Storage Temperature	-65°C to +150°C
Temperature (Ambient) Under Bias	–55°C to +125°C
DC Input Voltage with Respect to V _{CC}	-20V to +0.3V

OPERATING RANGE

Part Number	_V _{SS}	V _{DD}	V _{GG}	т _А
MM4025/6/7	+5.0V ±5%	ov	-12V ±10%	-55°C to +125°C
MM5025/6/7	+5.0V ±5%	ov	-12V ±10%	0°C to +70°C

ELECTRICAL CHARACTERISTICS OVER OPERATING RANGE (Unless Otherwise Noted)

arameters	Description	Test Condi	tions	Min.	Typ. (Note 1)	Max.	Units
v _{oH}	Output High Voltage	I _{OH} = -0.5mA		2.4		VSS	Volts
VOL	Output LOW Voltage	I _{OL} = 1.6mA		0.0		0.4	Volts
VIH	Input HIGH Level	Guaranteed input logical HIGH voltage for all inputs except clocks		V _{SS} −1.7		V _{SS} +0.3	Volts
VIL	Input LOW Level	Guaranteed input logical for all inputs except clock	•	V _{SS} -10		V _{SS} -4.2	Volts
I ₁	Input Leakage Current	V _{IN} = -10V, T _A = 25°C			10	500	nA
Ιφ	Clock Input Leakage Current	$V_{\phi} = -15V$, $T_{A} = 25^{\circ}C$			50	1000	nA
$V_{\phi H}$	Clock HIGH Level			V _{SS} -1.0		V _{SS} +0.3	Volts
$V_{\phi L}$	Clock LOW Level			V _{SS} -18.5		V _{SS} -14.5	Volts
		T _A = 25°C	.01MHz <f<0.1mhz< td=""><td></td><td>2</td><td>3.5</td><td></td></f<0.1mhz<>		2	3.5	
IGG	VGG Current	V _{SS} =5.0V, V _{GG} =-12.0V	f = 1.0MHz		2	3.5	mA
		$V_{\phi L} = -12.0V$	f = 3.0MHz		2	3.5	
		t = 115ns	.01MHz <f<0.1mhz< td=""><td></td><td>8</td><td>15</td><td></td></f<0.1mhz<>		8	15	
IDD	V _{DD} Current	Data = 11110000	f = 1.0MHz		22	32	mA
	_		f = 3.0MHz		48	70	

ote: 1. Typical Limits are at $V_{SS} = 5.0V$, $V_{GG} = -12.0V$ and 25° C ambient.

VITCHING CHARACTERISTICS AND OPERATING REQUIREMENTS OVER OPERATING RANGE

ameters	Definition	Test Conditions	Min.	Typ. (Note 1)	Max.	Units
	Data Rate (Note 2)	T _A = 0°C to +70°C	0.02		6.0	
f _D	Data hate (Note 2)	$T_A = -55^{\circ}C \text{ to } +125^{\circ}C$	0.12		2.0	MHz
	Clock Frequency (Note 3)	$T_A = 0^{\circ}C$ to $+70^{\circ}C$.01		3.0	WITZ
φ	Clock Frequency (Note of	T _A = -55° C to +125° C	0.06		1.0	
t φd	Delay Between Clocks (Note 3)		10		Note 3	ns
tφpw	Clock LOW Time	t _{ϕt} = 20ns	0.115		10	μs
φt	Clock Rise and Fall Times	10% to 90%			0.5	μς
ts	Set-Up Time, Data and Select Inputs				35	ns
	(See Definitions)					
th th	Hold Time, Data and Select Inputs (See Definitions)		20			ns
	Period From Start of (Note 3) One	$T_A = 0^{\circ} C \text{ to } +70^{\circ} C$	0.165		100	μs
фр	Phase to Start of Other Phase	$T_A = -55^{\circ}C \text{ to } +125^{\circ}C$	0.165		16.5	μο
pd	Delay, Clock to Data Out	C _L = 15pF			80	ns
(D)	Capacitance, Data Input	V _{IN} = 0, f = 1 MHz,			5	pF
(s)	Capacitance, Select Input or LC	All other pins GND (Note 4)			7	pF
;(_{\phi})	Capacitance, Clock Input	$V_{\phi} = 0$, f = 1MHz, All other pins GND	-	165	190	Pi

es: 2. The Data Rate is twice the frequency of either clock phase.

The maximum delay between clocks (φ₁ and φ₂ both HIGH) is a function of junction temperature. The junction temperature is a function of ambient temperature and clock duty cycle. See curves for minimum frequency on page 3.

^{4.} This parameter is periodically sampled but not 100% tested. It is guaranteed by design.

TRUTH TABLES

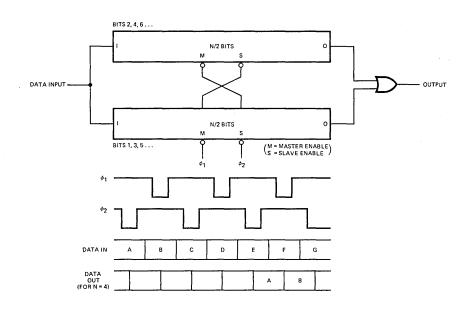
Am4025/5025 and Am4027/5027

LC	IN	OUT	DATA ENTERED
L	L	X	L
L	Н	X	Н
Н	Х	L	L
Н	Х	Н	н

Am4026/5026

IS	INPUT 1	INPUT 2	DATA ENTERED
L	L	Х	L
L	Н	×	Н
Н	Χ	L	L ·
Н	X	Н	Н

FUNCTIONAL EQUIVALENT OF EACH REGISTER



Since the two registers shift on opposite clock pulses, a new data bit is entered on both ϕ_1 and ϕ_2 . Data entering the register on ϕ_1 will appear at the output on ϕ_1 (from the negative edge of ϕ_1 to the negative edge of ϕ_2).

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DEFINITION OF TERMS

Dynamic Shift Register A shift register in which data storage occurs on small capacitive nodes rather than in bistable logic circuits. Dynamic shift registers must be clocked continuously to maintain the charge stored on the nodes.

 ϕ_1 , ϕ_2 The two clock pulses applied to the register. The clock is ON when it is at its negative voltage level and OFF when it is at V_{SS}. Data is accepted into the master of each bit during one phase and is transferred to the slave of each bit during the other phase.

 $t_{\varphi d}$ Clock delay time. The time elapsing between the LOW-to-HIGH transition of one clock input and the HIGH-to-LOW transition of the other clock input. During $t_{\varphi d}$ both clocks are HIGH and all data is stored on capacitive nodes.

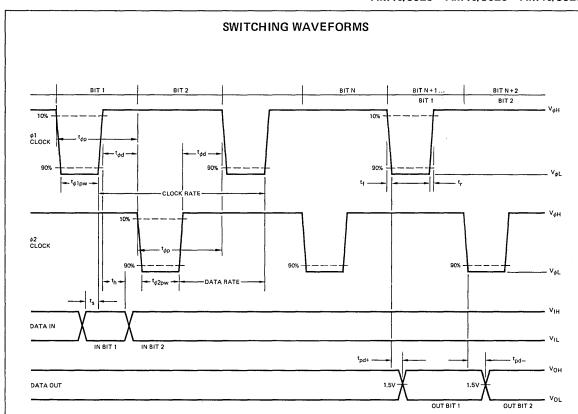
 $t_{\phi pw}$ Clock pulse width. The LOW time of each clock sign During $t_{\phi pw}$ one of the clocks is ON, and data transfer betwe master and slave or slave and master occurs.

 $t_{\phi t}$ Clock rise and fall times. The time required for the clc signals to change from 10% to 90% of the total level char occuring.

 $t_s(D)$ Data set-up time. The time prior to the LOW-to-HIC transition of ϕ during which the data on the data input must steady to be correctly written into the memory.

 $t_h(D)$ Data hold time. The time following the LOW-to-HII transition of ϕ during which the data must be steady. correctly write data into the register, the data must be applied $t_s(D)$ before this transition and must not be changed until t_h after this transition.

 t_{pd} The delay from a HIGH-to-LOW clock transition to corr data present at the register output.



Clock Rise Time 20ns Clock Fall Time 20ns Output Load 1 TTL Load

Metallization and Pad Layouts

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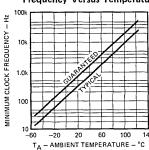
 v_{DD}

Am4027/5027

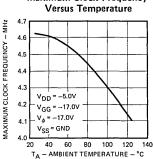
Am4025/5025 Am4026/5026 OUT A 1 OUT A 1-VSS OUT B OUT DIE SIZE 0.145" X 0.162" DIE SIZE 0.145" X 0.162" DIE SIZE 0.145" X 0.162"

OPERATING CHARACTERISTICS

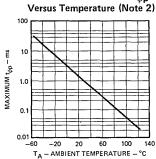
Guaranteed Minimum Clock Frequency Versus Temperature



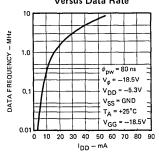
Maximum Clock Frequency



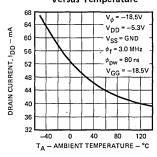
Guaranteed Maximum $t_{\phi p}$



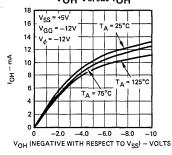
Typical Power Supply Current Versus Data Rate



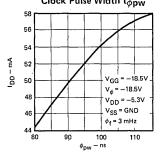
Typical Power Supply Current Versus Temperature



VOH Versus IOH



Typical Power Supply Current Versus Clock Pulse Width topw



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